

The 2N4351 is an enhancement mode N-Channel Mosfet

The 2N4351 is an enhancement mode N-Channel Mosfet designed for use as a General Purpose amplifier or switch

The hermetically sealed TO-72 package is well suited for high reliability and harsh environment applications.

(See Packaging Information).

2N4351 Features:

- Low ON Resistance
- Low Capacitance
- High Gain
- High Gate Breakdown Voltage
- Low Threshold Voltage

FEATURES

DIRECT REPLACEMENT FOR INTERSIL 2N4351

HIGH DRAIN CURRENT $I_D = 100\text{mA}$

HIGH GAIN $g_{fs} = 1000\mu\text{S}$

ABSOLUTE MAXIMUM RATINGS

@ 25°C (unless otherwise noted)

Maximum Temperatures

Storage Temperature -65°C to $+200^\circ\text{C}$

Operating Junction Temperature -55°C to $+150^\circ\text{C}$

Maximum Power Dissipation

Continuous Power Dissipation 375mW

MAXIMUM CURRENT

Drain to Source (Note 1) 100mA

MAXIMUM VOLTAGES

Drain to Body 25V

Drain to Source 25V

Peak Gate to Source (Note 2) $\pm 125\text{V}$

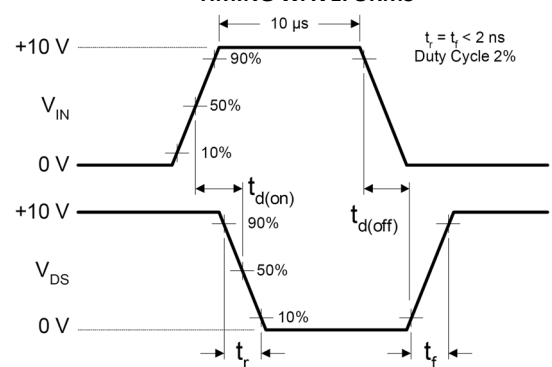
2N4351 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
BV_{DSS}	Drain to Source Breakdown Voltage	25	--	--	V	$I_D = 10\mu\text{A}$, $V_{GS} = 0\text{V}$
$V_{DS(on)}$	Drain to Source "On" Voltage	--	--	1		$I_D = 2\text{mA}$, $V_{GS} = 10\text{V}$
$V_{GS(th)}$	Gate to Source Threshold Voltage	1	--	5		$V_{DS} = 10\text{V}$, $I_D = 10\mu\text{A}$
I_{GSS}	Gate Leakage Current	--	--	10	pA	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$
I_{DSS}	Drain Leakage Current "Off"	--	--	10	nA	$V_{GS} = 10\text{V}$, $V_{DS} = 10\text{V}$
$I_{D(on)}$	Drain Current "On"	3	--	--	mA	$V_{GS} = 10\text{V}$, $V_{DS} = 10\text{V}$
g_{fs}	Forward Transconductance	1000	--	--	μS	$V_{DS} = 10\text{V}$, $I_D = 2\text{mA}$, $f = 1\text{MHz}$
$r_{DS(on)}$	Drain to Source "On" Resistance	--	--	300	Ω	$V_{GS} = 10\text{V}$, $I_D = 0\text{A}$, $f = 1\text{kHz}$
C_{rss}	Reverse Transfer Capacitance	--	--	1.3	pF	$V_{DS} = 0\text{V}$, $V_{GS} = 0\text{V}$, $f = 140\text{kHz}$
C_{iss}	Input Capacitance	--	--	5		$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 140\text{kHz}$
C_{db}	Drain to Body Capacitance	--	--	5.0		$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 140\text{kHz}$

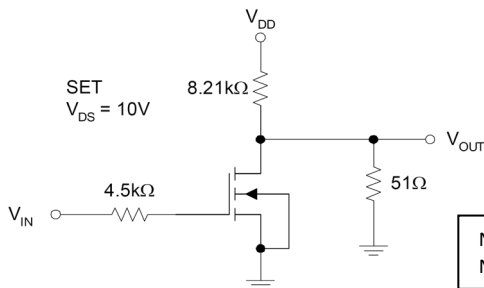
SWITCHING CHARACTERISTICS

SYMBOL	CHARACTERISTIC	MAX	UNITS
$t_{d(on)}$	Turn On Delay Time	45	ns
t_r	Turn On Rise Time	65	
$t_{d(off)}$	Turn Off Delay Time	60	
t_f	Turn Off Fall Time	100	

TIMING WAVEFORMS



SWITCHING TEST CIRCUIT



Note 1 - Absolute maximum ratings are limiting values above which 2N4351 serviceability may be impaired.
Note 2 - Device must not be tested at $\pm 125\text{V}$ more than once or longer than 300ms.

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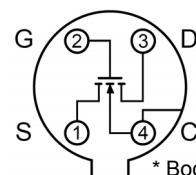
Web: <http://www.micross.com/distribution>

Available Packages:

2N4351 in TO-72

2N4351 in bare die.

TO-72 (Bottom View)



Please contact Micross for full package and die dimensions

* Body tied to case

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